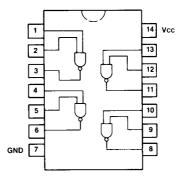
Quad 2-Input Positive NAND Gate

The LS00 is a bipolar, NPN, sealed-junction, silicon integrated circuit. It is manufactured in low-power Schottky technology and is available in a wire-bonded, 14-pin plastic DIP or surface mount package.



Electrical Characteristics

 $VCC = 5.0 \pm 0.5 \text{ V}, TA = -55 \text{ to } +125 ^{\circ}\text{C} \text{ (WA-LS)}$

 $VCC = 5.0 \pm 0.25 \text{ V}, TA = 0 \text{ to } 70^{\circ}\text{C (WP90222L1)}$

 $VCC = 5.0 \pm 0.5 \text{ V}$, TA = -40 to +85°C (WA-LSD, WP91397L1)

		WA	WA-LS		WP, WA-LSD	
Parameter	Symbol	Min	Max	Min	Max	Units
Output Voltage, Vcc = 4.5 V (WA-LS), 4.75 V (WP, WA-LSD) Low, loL = 4.0 mA loL = 8.0 mA High, loH = -0.4 mA	Vol Vol Voh	_ _ 2.5	0.4 0.5 —	_ _ 2.7	0.4 0.5 —	V V
Input Voltage, VCC = 4.5 V (WA-LS), 4.75 V (WP, WA-LSD) Low High Clamp, IIN = -18.0 mA	VIL VIH VIK	_ 2.0 _	0.7 7.5 –1.5	_ 2.0 _	0.8* 5.5 -1.5	V V V
Input Current, Vcc = 5.5 V (WA-LS), 5.25 V (WP, WA-LSD) Low, VIL = 0.4 V High, VIH = 2.7 V @ VI max, VI = 7.0 V (WA-LS), 5.5 V (WP, WA-LSD)	IIL IIH II	_ _ _	-0.4 20.0 0.1	_ _ _	-0.4 20.0 0.1	mA μA mA
Output Current, Vcc = 5.5 V (WA-LS), 5.25 V (WP, WA-LSD) Short-Circuit	los	-20.0	-100.0	-20.0	-100.0	mA
Supply Current, VCC = 5.5 V (WA-LS), 5.25 V (WP, WA-LSD) Output Low Output High	ICCL ICCH		4.4 1.6		4.4 1.6	mA mA

^{*} WA-LSD, WP91397L1: VIL = 0.7 V

Timing Characteristics

VCC = 5.0 V, $TA = 25^{\circ}C$, CL = 15 pF

	Symbol	WA-LS		WP, W		
Parameter		Min	Max	Min	Max	Units
Propagation Delay Low-to-High High-to-Low	tplh tphl	_	10.0 10.0	_ _	15.0 15.0	ns ns

Maximum Ratings

 Power supply voltage (VCC)
 7.0 V

 Operating temperature (TA)
 WA-LS: -55 to +125°C

 WP90222L1: 0 to 70°C

 WA-LSD, WP91397L1: -40 to +85°C

 Storage temperature (Tstg)
 -65 to +150°C

Maximum ratings are defined as the limiting conditions that the user can apply to the device under all variations of circuit and environmental conditions. If any rating is exceeded, permanent damage to the device may result.

Bonding or soldering of the external leads of this device can be performed safely at temperatures up to 300°C.